PATENT ABSTRACTS OF JAPAN

(11)Publication number:

05-074717

(43)Date of publication of application: 26.03.1993

(51)Int.CI. H01L 21/205 B01J 23/38 C30B 25/14 C30B 29/40

(21)Application number : 03-230656 (71)Applicant : FUJITSU LTD

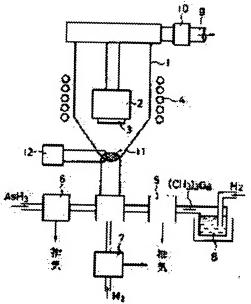
(22)Date of filing: 11.09.1991 (72)Inventor: OTSUKA NOBUYUKI

(54) COMPOUND SEMICONDUCTOR CRYSTAL GROWTH METHOD

(57)Abstract:

PURPOSE: To epitaxially grow an atomic layer of good quality using a small quantity of raw gas by enhancing the reactive efficiency of the raw gas by introducing a catalyst into a growth device.

CONSTITUTION: A substrate 3 is heated up using a high frequency heater 4. After a quartz reaction tube 1 has been purged by feeding hydrogen gas into it through a valve 7, (CH3) 3Ga is vaporized using a bubbler 8, and the (CH3)3Ga is fed into the quartz reactor tube 1 through a switching valve 5. Then, after the quartz reaction tube 1 has been purged by feeding hydrogen gas again, AsH3 is fed through a switching valve 6, and the catalyst 11 introduced into a growth device is heated up using a power source 12. As a result, the partial contact of the AsH3 to be fed as the raw material of arsenic, is accelerated by a catalytic action, and the feeding efficiency of arsenic can be improved. Accordingly, an atomic layer can be grown by a little feeding quantity of AsH3.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rej ction]

[Date of xtinction of right]